

# Fangfei Ming

## List of Publications by Year in descending order

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docs citations

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times ranked

291  
citing authors

#	ARTICLE	IF	CITATIONS
1	Controlled Implantation of Phosphorous Atoms into a Silicon Surface Lattice with a Scanning Tunneling Microscopy Tip. ACS Applied Electronic Materials, 2021, 3, 3338-3345.	4.3	1
2	Superconductivity in a Hole-Doped Mott-Insulating Triangular Adatom Layer on a Silicon Surface. Physical Review Letters, 2020, 125, 117001.	7.8	26
3	Coupled Sublattice Melting and Charge-Order Transition in Two Dimensions. Physical Review Letters, 2020, 124, 097602.	7.8	8
4	Zero-bias anomaly in nanoscale hole-doped Mott insulators on a triangular silicon surface. Physical Review B, 2018, 97, .	3.2	11
5	Atomic and electronic structure of doped $\text{Si}/\text{Sn}$ interfaces. Physical Review B, 2018, 97, .	3.2	11
6	Hidden phase in a two-dimensional Sn layer stabilized by modulation hole doping. Nature Communications, 2017, 8, 14721.	12.8	17
7	Adsorption and spin-related properties of multi-Co atoms assembled in the half unit cells of Si(111)-(7 $\text{\AA}$ -) $\sqrt{3} \times \sqrt{3}$ R120. Physical Review Letters, 2017, 119, 266802.	7.8	33
8	Realization of a Hole-Doped Mott Insulator on a Triangular Silicon Lattice. Physical Review Letters, 2017, 119, 266802.	7.8	33
9	Controllable dissociations of $\text{PH}_3$ molecules on Si(001). Nanotechnology, 2016, 27, 135704.	2.6	7
10	Mapping potential energy landscape of a probing atom in a complex surface environment. Physical Review B, 2015, 92, .	3.2	2
11	Controlling adsorption and spin configurations of Co atoms on $\text{Si}(111)-(7 \times 7)$ surface. Physical Review B, 2015, 91, .	3.2	2
12	Equivalence of electronic and mechanical stresses in structural phase stabilization: A case study of indium wires on Si(111). Physical Review B, 2015, 91, .	3.2	10
13	Stabilization and Manipulation of Electronically Phase-Separated Ground States in Defective Indium Atom Wires on Silicon. Physical Review Letters, 2014, 113, 196802.	7.8	22
14	Superconductivity of individual Pb islands on Si(111): pseudogap, critical region, density of states, and island size. Superconductor Science and Technology, 2013, 26, 085009.	3.5	8
15	Probing the generalized magicity of Ag nanoclusters constructed on Si(111) by atomic manipulation. Physical Review B, 2013, 88, .	3.2	7
16	Identifying the Numbers of Ag Atoms in Their Nanostructures Grown on a Si(111)-(7 $\text{\AA}$ -7) Surface. Journal of Physical Chemistry C, 2011, 115, 3847-3853.	3.1	11
17	Assembling and Disassembling Ag Clusters on Si(111)-(7 $\text{\AA}$ -7) by Vertical Atomic Manipulation. ACS Nano, 2011, 5, 7608-7616.	14.6	30
18	Size-dependent superconducting state of individual nanosized Pb islands grown on Si(111) by tunneling spectroscopy. Journal of Physics Condensed Matter, 2011, 23, 265007.	1.8	9

#	ARTICLE	IF	CITATIONS
19	Interface effects on the quantum well states of Pb thin films. Journal of Physics Condensed Matter, 2011, 23, 485001.	1.8	5
20	Study of CO diffusion on stepped Pt(111) surface by scanning tunneling microscopy. Surface Science, 2010, 604, 322-326.	1.9	8
21	Effect of substrate doping concentration on quantum well states of Pb island grown on Si(111). Surface Science, 2010, 604, 175-180.	1.9	4
22	Electrical rectification by selective wave-function coupling in small Ag clusters on $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline" \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mtext} \rangle \text{Si} \langle \text{mml:mrow} \rangle \langle \text{mml:mo} \rangle \langle \text{mml:mrow} \rangle \langle \text{mml:mn} \rangle 111 \langle \text{mml:mn} \rangle$ Physical Review B, 2010, 81, .	1.2	11